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STMicroelectronics - STM32F437VGT6 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f437vgt6

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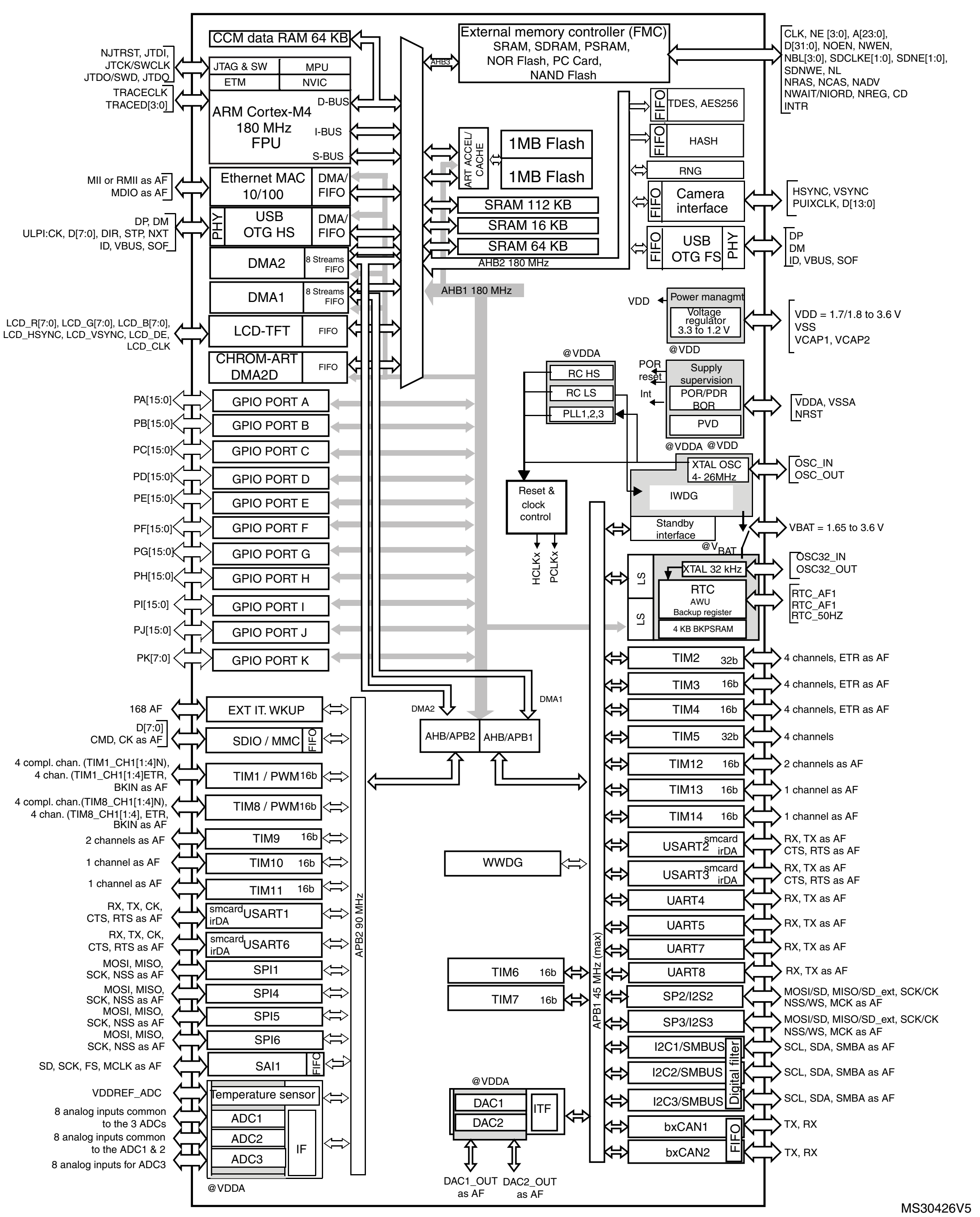
Figure 4. STM32F437xx and STM32F439xx block diagram



1. The timers connected to APB2 are clocked from TIMxCLK up to 180 MHz, while the timers connected to APB1 are clocked from TIMxCLK either up to 90 MHz or 180 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.
2. The LCD-TFT is available only on STM32F439xx devices.

3.21 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery, an external supercapacitor, or from V_{DD} when no external battery and an external supercapacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT}, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When PDR_ON pin is not connected to V_{DD} (Internal Reset OFF), the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to VDD.

3.22 Timers and watchdogs

The devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

Table 6 compares the features of the advanced-control, general-purpose and basic timers.

4. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F4xx reference manual, available from the STMicroelectronics website: *www.st.com*.
5. FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
6. If the device is delivered in an WLCSP143, UFBGA169, UFBGA176, LQFP176 or TFBGA216 package, and the BYPASS_REG pin is set to V_{DD} (Regulator OFF/internal reset ON mode), then PA0 is used as an internal Reset (active low).
7. PI0 and PI1 cannot be used for I2S2 full-duplex mode.
8. The DCMI_VSYNC alternate function on PG9 is only available on silicon revision 3.

Table 12. STM32F437xx and STM32F439xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/2/3/4/5/6	SPI2/3/SAI1	SPI3/USART1/2/3	USART6/UART4/5/7/8	CAN1/2/TIM12/13/14/LCD	OTG2_HS/OTG1_FS	ETH	FMC/SDIO/OTG2_FS	DCMI	LCD	SYS
Port C	PC8	-	-	TIM3_CH3	TIM8_CH3	-	-	-	-	USART6_CK	-	-	-	SDIO_D0	DCMI_D2	-	EVENTOUT
	PC9	MCO2	-	TIM3_CH4	TIM8_CH4	I2C3_SDA	I2S_CKIN	-	-	-	-	-	-	SDIO_D1	DCMI_D3	-	EVENTOUT
	PC10	-	-	-	-	-	-	SPI3_SCK/I2S3_CK	USART3_TX	UART4_TX	-	-	-	SDIO_D2	DCMI_D8	LCD_R2	EVENTOUT
	PC11	-	-	-	-	-	I2S3ext_SD	SPI3_MISO	USART3_RX	UART4_RX	-	-	-	SDIO_D3	DCMI_D4	-	EVENTOUT
	PC12	-	-	-	-	-	-	SPI3_MOSI/I2S3_SD	USART3_CK	UART5_TX	-	-	-	SDIO_CK	DCMI_D9	-	EVENTOUT
	PC13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PC14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PC15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
Port D	PD0	-	-	-	-	-	-	-	-	-	CAN1_RX	-	-	FMC_D2	-	-	EVENTOUT
	PD1	-	-	-	-	-	-	-	-	-	CAN1_TX	-	-	FMC_D3	-	-	EVENTOUT
	PD2	-	-	TIM3_ETR	-	-	-	-	-	UART5_RX	-	-	-	SDIO_CMD	DCMI_D11	-	EVENTOUT
	PD3	-	-	-	-	-	SPI2_SCK/I2S2_CK	-	USART2_CTS	-	-	-	-	FMC_CLK	DCMI_D5	LCD_G7	EVENTOUT
	PD4	-	-	-	-	-	-	-	USART2_RTS	-	-	-	-	FMC_NOE	-	-	EVENTOUT
	PD5	-	-	-	-	-	-	-	USART2_TX	-	-	-	-	FMC_NWE	-	-	EVENTOUT
	PD6	-	-	-	-	-	SPI3_MOSI/I2S3_SD	SAI1_SD_A	USART2_RX	-	-	-	-	FMC_NWAIT	DCMI_D10	LCD_B2	EVENTOUT

Table 13. STM32F437xx and STM32F439xx register boundary addresses (continued)

Bus	Boundary address	Peripheral
	0x4008 0000- 0x4FFF FFFF	Reserved
AHB1	0x4004 0000 - 0x4007 FFFF	USB OTG HS
	0x4002 BC00- 0x4003 FFFF	Reserved
	0x4002 B000 - 0x4002 BBFF	DMA2D
	0x4002 9400 - 0x4002 AFFF	Reserved
	0x4002 9000 - 0x4002 93FF	ETHERNET MAC
	0x4002 8C00 - 0x4002 8FFF	
	0x4002 8800 - 0x4002 8BFF	
	0x4002 8400 - 0x4002 87FF	
	0x4002 8000 - 0x4002 83FF	
	0x4002 6800 - 0x4002 7FFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0X4002 5000 - 0X4002 5FFF	Reserved
	0x4002 4000 - 0x4002 4FFF	BKPSRAM
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0X4002 3400 - 0X4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2C00 - 0x4002 2FFF	Reserved
	0x4002 2800 - 0x4002 2BFF	GPIOK
	0x4002 2400 - 0x4002 27FF	GPIOJ
	0x4002 2000 - 0x4002 23FF	GPIOI
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1800 - 0x4002 1BFF	GPIOG
	0x4002 1400 - 0x4002 17FF	GPIOF
	0x4002 1000 - 0x4002 13FF	GPIOE
	0X4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA

Table 18. Limitations depending on the operating power supply range

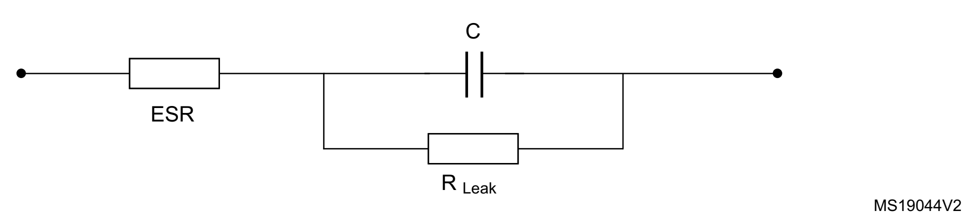
Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum HCLK frequency vs Flash memory wait states [1][2]	I/O operation	Possible Flash memory operations
V_{DD} =1.7 to 2.1 V[3]	Conversion time up to 1.2 Msps	20 MHz[4]	168 MHz with 8 wait states and over-drive OFF	No I/O compensation	8-bit erase and program operations only
V_{DD} = 2.1 to 2.4 V	Conversion time up to 1.2 Msps	22 MHz	180 MHz with 8 wait states and over-drive ON	No I/O compensation	16-bit erase and program operations
V_{DD} = 2.4 to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	180 MHz with 7 wait states and over-drive ON	I/O compensation works	16-bit erase and program operations
V_{DD} = 2.7 to 3.6 V[5]	Conversion time up to 2.4 Msps	30 MHz	180 MHz with 5 wait states and over-drive ON	I/O compensation works	32-bit erase and program operations

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to *Section 3.17.2: Internal reset OFF*).
4. Prefetch is not available.
5. The voltage range for USB full speed PHYs can drop down to 2.7 V. However the electrical characteristics of D- and D+ pins will be degraded between 2.7 and 3 V.

6.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor C_{EXT} to the VCAP1/VCAP2 pins. C_{EXT} is specified in *Table 19*.

Figure 24. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

Table 19. VCAP1/VCAP2 operating conditions(1)

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor	2.2 µF
ESR	ESR of external capacitor	< 2 Ω

1. When bypassing the voltage regulator, the two 2.2 µF V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A.

Table 20. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	µs/V
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A.

Table 21. Operating conditions at power-up / power-down (regulator OFF)(1)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	µs/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

Additional current consumption

The MCU is placed under the following conditions:

- All I/O pins are configured in analog mode.
- The Flash memory access time is adjusted to fHCLK frequency.
- The voltage scaling is adjusted to fHCLK frequency as follows:
  - Scale 3 for $f_{HCLK} \leq 120$ MHz,
  - Scale 2 for 120 MHz < $f_{HCLK} \leq 144$ MHz
  - Scale 1 for 144 MHz < $f_{HCLK} \leq 180$ MHz. The over-drive is only ON at 180 MHz.
- The system clock is HCLK, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
- HSE crystal clock frequency is 25 MHz.
- When the regulator is OFF, V12 is provided externally as described in *Table 17: General operating conditions*
- T_A= 25 °C .

Table 30. Typical current consumption in Run mode, code with data processing running from Flash memory or RAM, regulator ON (ART accelerator enabled except prefetch), V_{DD}=1.7 V[1]

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Unit
I_{DD}	Supply current in RUN mode from V_{DD} supply	All Peripheral enabled	168	88.2	mA
			150	74.3	
			144	71.3	
			120	52.9	
			90	42.6	
			60	28.6	
			30	15.7	
			25	12.3	
		All Peripheral disabled	168	40.6	
			150	30.6	
			144	32.6	
			120	24.7	
			90	19.7	
			60	13.6	
			30	7.7	
			25	6.7	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherls (such as ADC, or DAC) is not included.

Table 31. Typical current consumption in Run mode, code with data processing running from Flash memory, regulator OFF (ART accelerator enabled except prefetch)(1)

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	VDD=3.3 V		VDD=1.7 V		Unit
				I_{DD12}	I_{DD}	I_{DD12}	I_{DD}	
I_{DD12} / I_{DD}	Supply current in RUN mode from V_{12} and V_{DD} supply	All Peripherals enabled	168	77.8	1.3	76.8	1.0	mA
			150	70.8	1.3	69.8	1.0	
			144	64.5	1.3	63.6	1.0	
			120	49.9	1.2	49.3	0.9	
			90	39.2	1.3	38.7	1.0	
			60	27.2	1.2	26.8	0.9	
			30	15.6	1.2	15.4	0.9	
			25	13.6	1.2	13.5	0.9	
		All Peripherals disabled	168	38.2	1.3	37.0	1.0	
			150	34.6	1.3	33.4	1.0	
			144	31.3	1.3	30.3	1.0	
			120	24.0	1.2	23.2	0.9	
			90	18.1	1.4	18.0	1.0	
			60	12.9	1.2	12.5	0.9	
			30	7.2	1.2	6.9	0.9	
			25	6.3	1.2	6.1	0.9	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

Table 35. Peripheral current consumption (continued)

Peripheral		I_{DD}(Typ)(1)			Unit
		Scale 1	Scale 2	Scale 3	
APB2 (up to 90 MHz)	SDIO	8.11	8.75	7.83	µA/MHz
	TIM1	17.11	15.97	14.17	
	TIM8	17.33	16.11	14.33	
	TIM9	7.22	6.67	6.00	
	TIM10	4.56	4.31	3.83	
	TIM11	4.78	4.44	4.00	
	ADC1(5)	4.67	4.31	3.83	
	ADC2(5)	4.78	4.44	4.00	
	ADC3(5)	4.56	4.17	3.67	
	SPI1	1.44	1.39	1.17	
	USART1	4.00	3.75	3.33	
	USART6	4.00	3.75	3.33	
	SPI4	1.44	1.39	1.17	
	SPI5	1.44	1.39	1.17	
	SPI6	1.44	1.39	1.17	
	SYSCFG	0.78	0.69	0.67	
	LCD_TFT	39.89	37.22	33.17	
	SAI1	3.78	3.47	3.17	

1. When the I/O compensation cell is ON, I_{DD} typical value increases by 0.22 mA.
2. The BusMatrix is automatically active when at least one master is ON.
3. To enable an I2S peripheral, first set the I2SMOD bit and then the I2SE bit in the SPI_I2SCFGR register.
4. When the DAC is ON and EN1/2 bits are set in DAC_CR register, add an additional power consumption of 0.8 mA per DAC channel for the analog part.
5. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 36* and *Table 58*, respectively.

Unless otherwise specified, the parameters given in *Table 58* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 58. I/O AC characteristics(1)(2)

OSPEEDRy [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DD} \geq$ 2.7 V	-	-	4	MHz
			C_L = 50 pF, $V_{DD} \geq$ 1.7 V	-	-	2	
			C_L = 10 pF, $V_{DD} \geq$ 2.7 V	-	-	8	
			C_L = 10 pF, $V_{DD} \geq$ 1.8 V	-	-	4	
			C_L = 10 pF, $V_{DD} \geq$ 1.7 V	-	-	3	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} = 1.7 V to 3.6 V	-	-	100	ns
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, $V_{DD} \geq$ 2.7 V	-	-	25	MHz
			C_L = 50 pF, $V_{DD} \geq$ 1.8 V	-	-	12.5	
			C_L = 50 pF, $V_{DD} \geq$ 1.7 V	-	-	10	
			C_L = 10 pF, $V_{DD} \geq$ 2.7 V	-	-	50	
			C_L = 10 pF, $V_{DD} \geq$ 1.8 V	-	-	20	
			C_L = 10 pF, $V_{DD} \geq$ 1.7 V	-	-	12.5	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, $V_{DD} \geq$ 2.7 V	-	-	10	ns
			C_L = 10 pF, $V_{DD} \geq$ 2.7 V	-	-	6	
			C_L = 50 pF, $V_{DD} \geq$ 1.7 V	-	-	20	
			C_L = 10 pF, $V_{DD} \geq$ 1.7 V	-	-	10	
10	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 40 pF, $V_{DD} \geq$ 2.7 V	-	-	50(4)	MHz
			C_L = 10 pF, $V_{DD} \geq$ 2.7 V	-	-	100(4)	
			C_L = 40 pF, $V_{DD} \geq$ 1.7 V	-	-	25	
			C_L = 10 pF, $V_{DD} \geq$ 1.8 V	-	-	50	
			C_L = 10 pF, $V_{DD} \geq$ 1.7 V	-	-	42.5	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 40 pF, $V_{DD} \geq$ 2.7 V	-	-	6	ns
			C_L = 10 pF, $V_{DD} \geq$ 2.7 V	-	-	4	
			C_L = 40 pF, $V_{DD} \geq$ 1.7 V	-	-	10	
			C_L = 10 pF, $V_{DD} \geq$ 1.7 V	-	-	6	

6.3.26 FMC characteristics

Unless otherwise specified, the parameters given in *Table 86* to *Table 101* for the FMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10 except at V_{DD} range 1.7 to 2.1V where OSPEEDRy[1:0] = 11
- Measurement points are done at CMOS levels: $0.5V_{DD}$

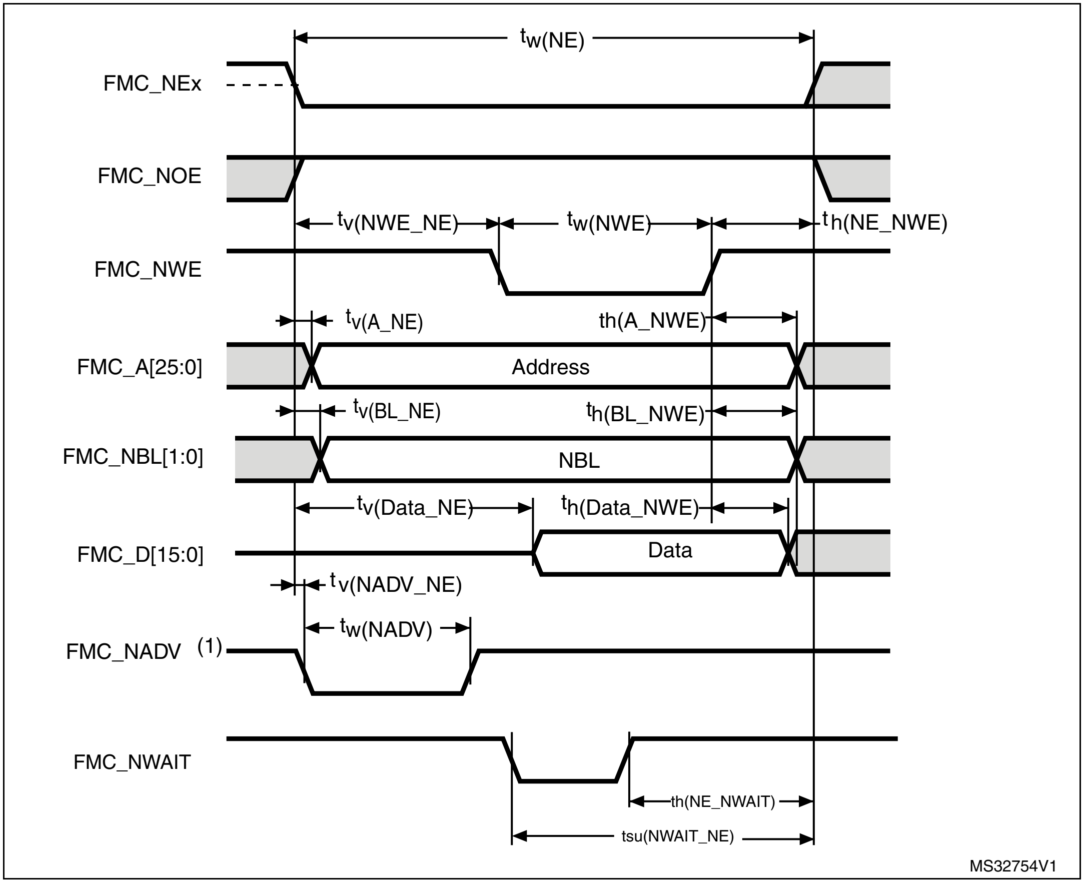
Refer to *Section 6.3.17: I/O port characteristics* for more details on the input/output characteristics.

Asynchronous waveforms and timings

Figure 55 through *Figure 58* represent asynchronous waveforms and *Table 86* through *Table 93* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime = 0x1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1 (except for asynchronous NWAIT mode , DataSetupTime = 0x5)
- BusTurnAroundDuration = 0x0
- For SDRAM memories, V_{DD} ranges from 2.7 to 3.6 V and maximum frequency FMC_SDCLK = 90 MHz
- For Mobile LPSDR SDRAM memories, V_{DD} ranges from 1.7 to 1.95 V and maximum frequency FMC_SDCLK = 84 MHz

Figure 56. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms



1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.

Table 88. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}$	$3T_{HCLK}$+1	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	T_{HCLK} – 0.5	T_{HCLK}+ 0.5	ns
$t_{w(NWE)}$	FMC_NWE low time	T_{HCLK}	T_{HCLK}+ 0.5	ns
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	T_{HCLK} +1.5	-	ns
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	ns
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	T_{HCLK}+0.5	-	ns
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	1.5	ns
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	T_{HCLK}+0.5	-	ns
$t_{v(Data\_NE)}$	Data to FMC_NEx low to Data valid	-	T_{HCLK}+ 2	ns
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	T_{HCLK}+0.5	-	ns
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	0.5	ns
$t_{w(NADV)}$	FMC_NADV low time	-	T_{HCLK}+ 0.5	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 99. Switching characteristics for PC Card/CF read and write cycles in I/O space[(1)(2)]

Symbol	Parameter	Min	Max	Unit
tw(NIOWR)	FMC_NIOWR low width	$8T_{HCLK} - 0.5$	-	ns
tv(NIOWR-D)	FMC_NIOWR low to FMC_D[15:0] valid	-	0	ns
th(NIOWR-D)	FMC_NIOWR high to FMC_D[15:0] invalid	$9T_{HCLK} - 2$	-	ns
td(NCE4_1-NIOWR)	FMC_NCE4_1 low to FMC_NIOWR valid	-	$5T_{HCLK}$	ns
th(NCEx-NIOWR)	FMC_NCEx high to FMC_NIOWR invalid	$5T_{HCLK}$	-	ns
td(NIORD-NCEx)	FMC_NCEx low to FMC_NIORD valid	-	$5T_{HCLK}$	ns
th(NCEx-NIORD)	FMC_NCEx high to FMC_NIORD) valid	$6T_{HCLK}+2$	-	ns
tw(NIORD)	FMC_NIORD low width	$8T_{HCLK} - 0.5$	$8T_{HCLK}+0.5$	ns
tsu(D-NIORD)	FMC_D[15:0] valid before FMC_NIORD high	T_{HCLK}	-	ns
td(NIORD-D)	FMC_D[15:0] valid after FMC_NIORD high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

NAND controller waveforms and timings

Figure 69 through *Figure 72* represent synchronous waveforms, and *Table 100* and *Table 101* provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01;
- COM.FMC_WaitSetupTime = 0x03;
- COM.FMC_HoldSetupTime = 0x02;
- COM.FMC_HiZSetupTime = 0x01;
- ATT.FMC_SetupTime = 0x01;
- ATT.FMC_WaitSetupTime = 0x03;
- ATT.FMC_HoldSetupTime = 0x02;
- ATT.FMC_HiZSetupTime = 0x01;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 76. LCD-TFT horizontal timing diagram

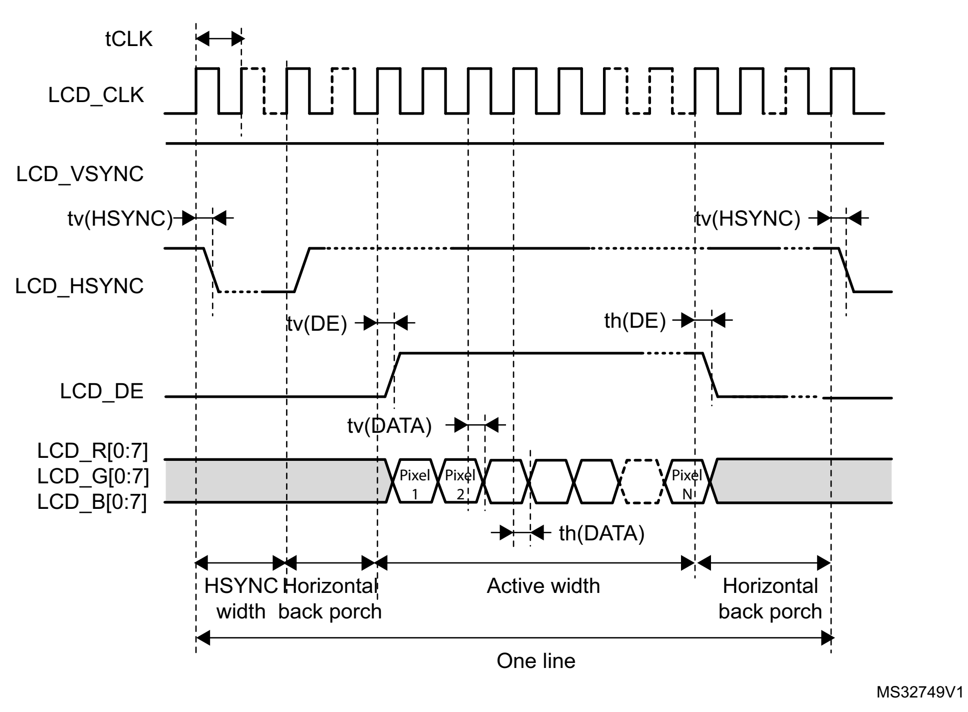


Figure 77. LCD-TFT vertical timing diagram

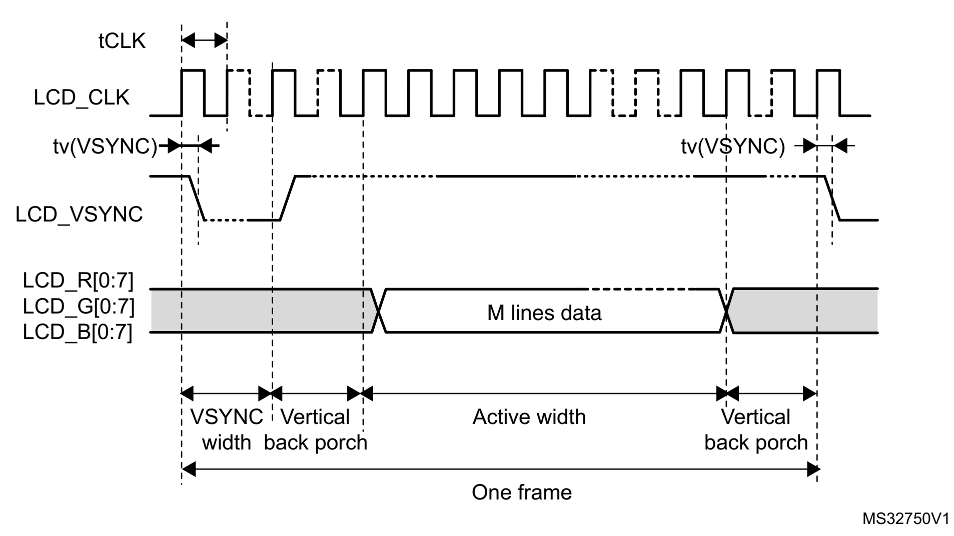


Table 111. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	0.155	0.175	0.195	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	4.486	4.521	4.556	0.1766	0.1780	0.1794
E	5.512	5.547	5.582	0.2170	0.2184	0.2198
e	-	0.400	-	-	0.0157	-
e1	-	4.000	-	-	0.1575	-
e2	-	4.800	-	-	0.1890	-
F	-	0.2605	-	-	0.0103	-
G	-	0.3735	-	-	0.0147	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 84. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale recommended footprint

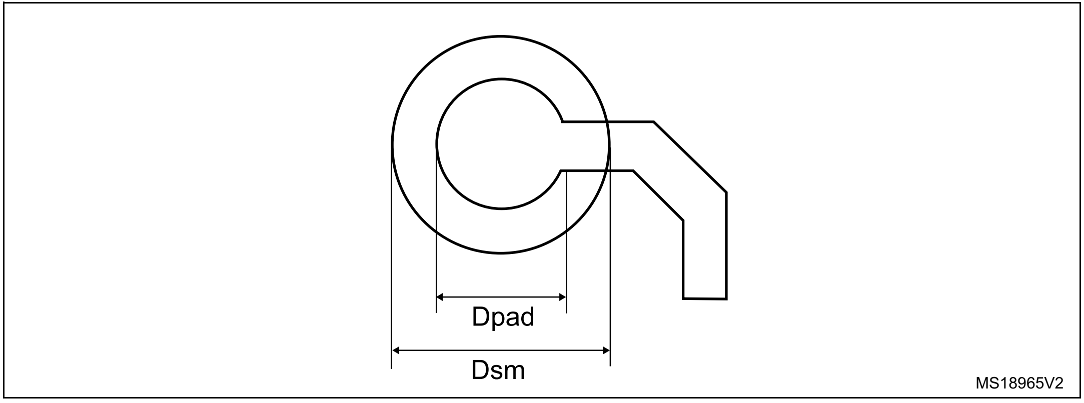
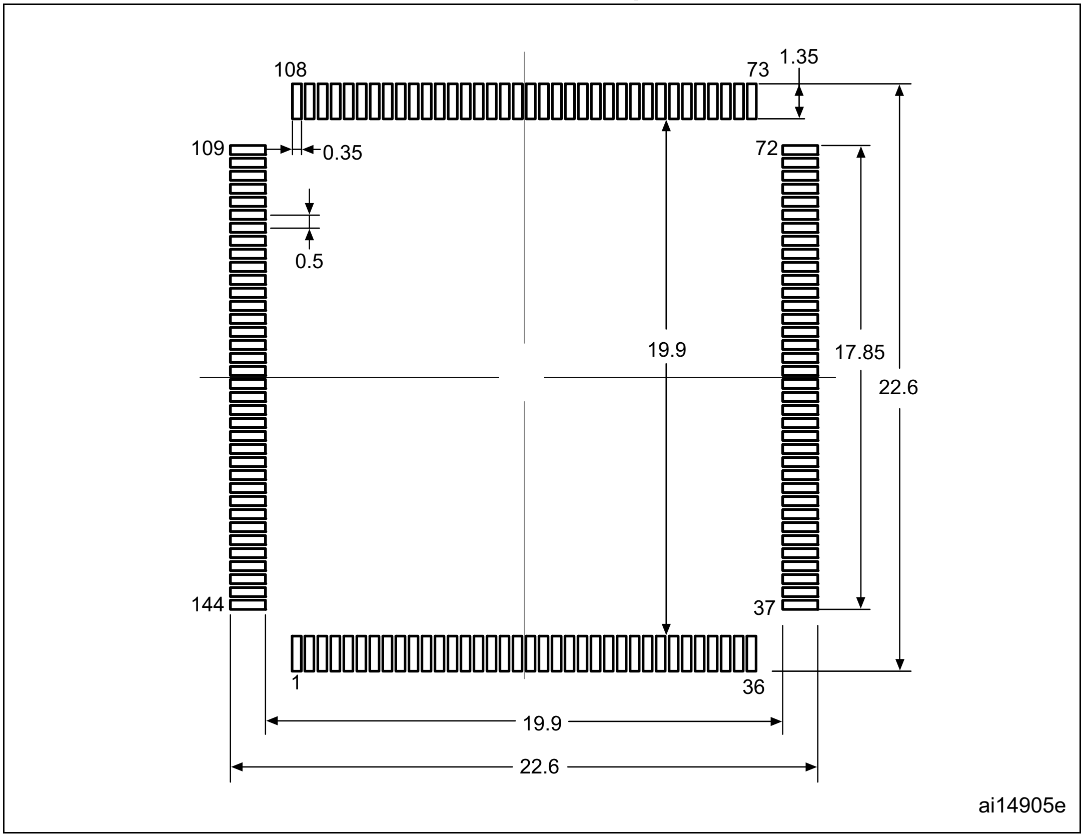


Figure 87. LQPF144- 144-pin,20 x 20 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.